NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TVU014** is Designed for

FEATURES:

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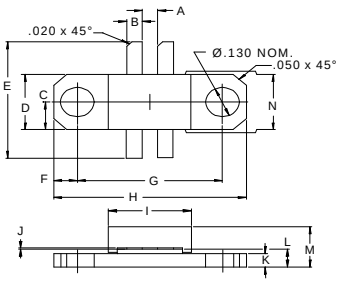
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	2 x 2.6 A
V_{CBO}	45 V
V_{CEO}	25 V
V_{EBO}	4.0 V
P_{DISS}	65 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.5 °C/W

PACKAGE STYLE .250 BAL FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.060 / 1.52	
B	.055 / 1.40	.065 / 1.65
C	.125 / 3.18	
D	.243 / 6.17	.255 / 6.48
E	.630 / 16.00	.670 / 17.01
F	.092 / 2.34	
G	.555 / 14.10	.565 / 14.35
H	.739 / 18.77	.750 / 19.05
I	.315 / 8.00	.327 / 8.31
J	.002 / 0.05	.006 / 0.15
K	.055 / 1.40	.065 / 1.65
L	.075 1.91	.095 / 2.41
M		.190 / 4.83
N	.245 / 6.22	.257 / 6.53

ORDER CODE: ASI10647

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 20 mA	45			V
BV_{CEO}	I_C = 40 mA	25			V
BV_{EBO}	I_E = 5.0 mA	3.0			V
h_{FE}	V_{CE} = 20 V I_C = 0.5 A	10		---	---
C_{OB}	V_{CB} = 25 V f = 1.0 MHz			20	pF
P_G	V_{CE} = 25 V I_C = 2 x 850 mA f = 860 MHz	8.5			dB
IMD_1	P_{OUT} = 14 W	-50			dBc